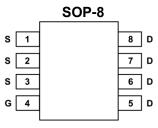
AO4419-HX P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V) R _{DS(on)} (Ω) Qg (Typ.) I _D (A)				
-30	0.018 at Vgs = - 10 V	12mC	-9.0	
	0.024 at Vgs = - 4.5 V	13nC	-7.8	





Top View

FEATURES

- TrenchFET® Power MOSFET
- 100 % R_q Tested

APPLICATIONS

- Load Switch
- Battery Switch

Absolute Maximum Ratings						
	Parameter	Max.	Units			
VDS	Drain-to-Source Voltage	-30	.,,			
Vgs	Gate-to-Source Voltage	± 20	V			
I _D @ T _A = 25°C	Continuous Drain Current, V _{GS} @ 10V	-9.2				
I _D @ T _A = 70°C	Continuous Drain Current, V _{GS} @ 10V	-7.3	Α			
IDM	Pulsed Drain Current ①	-75				
PD @T _A = 25°C	Power Dissipation ④	2.5	10/			
P _D @T _A = 70°C	Power Dissipation ④	1.6	W			
	Linear Derating Factor	0.02	W/°C			
TJ	Operating Junction and	-55 to + 150				
Тѕтс	Storage Temperature Range	33 10 1 130	°C			

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Static @ TJ = 25°C (unless otherwise specified)							
	Parameter	Min.	Тур.	Max.	Units	Conditions	
BV _{DSS}	Drain-to-Source Breakdown Voltage	-30			V	$V_{GS} = 0V, I_{D} = -250\mu A$	
ΔBVpss/ΔTJ	Breakdown Voltage Temp. Coefficient		0.019		V/°C	Reference to 25°C, I _D = -1mA	
RDS(on)			15.6	19.4		V _{GS} = -10V, I _D = -9.2A ③	
	Static Drain-to-Source On-Resistance		25.6	32.5	mΩ	V_{GS} = -4.5V, I_{D} = -7.5A \odot	
VGS(th)	Gate Threshold Voltage	-1.3	-1.8	-2.4	V	N/ N/ 1 05 A	
ΔV GS(th)	Gate Threshold Voltage Coefficient		-5.7		mV/°C	$V_{DS} = V_{GS}$, $I_D = -25\mu A$	
IDSS	Drain-to-Source Leakage Current			-1.0		$V_{DS} = -24V, V_{GS} = 0V$	
	- X			-150	μA	V _{DS} = -24V, V _{GS} = 0V, T _J = 125°C	
Igss	Gate-to-Source Forward Leakage			-100		V _{GS} = -20V	
	Gate-to-Source Reverse Leakage			100	nA	V _{GS} = 20V	
gfs	Forward Transconductance	13			S	V _{DS} = -10V, I _D = -7.5A	
Q_g	Total Gate Charge ®		14		nC	V_{DS} = -15V, V_{GS} = -4.5V, I_{D} = -7.5A	
Q_g	Total Gate Charge ®		25	38		V _{GS} = -10V	
Q_{gs}	Gate-to-Source Charge ®		3.5		nC	V _{DS} = -15V	
Q_{gd}	Gate-to-Drain Charge ⑥		6.4			$I_D = -7.5A$	
R_G	Gate Resistance ®		15		Ω		
td(on)	Turn-On Delay Time		16			V _{DD} = -15V, V _{GS} = -4.5V ③	
t _r	Rise Time		44			I _D = -1.0A	
td(off)	Turn-Off Delay Time		55		ns	$R_G = 6.8\Omega$	
t _f	Fall Time		49			See Figs. 20a &20b	
C _{iss}	Input Capacitance		1110			V _{GS} = 0V	
Coss	Output Capacitance		230		pF	$V_{DS} = -25V$ f = 1.0MHz	
C _{rss}	Reverse Transfer Capacitance		160				

Avalanche Characteristics					
	Parameter	Тур.	Max.	Units	
Eas	Single Pulse Avalanche Energy ②		100	mJ	
lar	Avalanche Current ①		-7.5	А	

Dio	Diode Characteristics						
	Parameter	Min.	Тур.	Max.	Unit	Conditions	
Is	Continuous Source Current (Body Diode)			-2.5			
Isм	Pulsed Source Current (Body Diode) ①			-75	Α		
VsD	Diode Forward Voltage			-1.2	V	T _J = 25°C, I _S = -2.5A, V _G S = 0V ③	
trr	Reverse Recovery Time		24	36		T _J = 25°C, I _F = -2.5A, V _{DD} = -24V	
Q _{rr}	Reverse Recovery Charge		15	23	nC	di/dt = 100A/µs ③	

Thermal Resistance					
	Parameter	Тур.	Max.	Units	
Rejl	Junction-to-Drain Lead ⑤		20	0000	
Reja	Junction-to-Ambient ④		50	°C/W	

Notes

- Repetitive rating; pulse width limited by max. junction temperature.
 Starting TJ = 25°C, L = 3.5mH, RG = 25Ω, IAS = -7.5A.
 Pulse width ≤ 400µs; duty cycle ≤ 2%.
 When mounted on 1 inch square copper board.
 Rθ is measured at TJ of approximately 90°C.
 For DESIGN AID ONLY, not subject to production testing.

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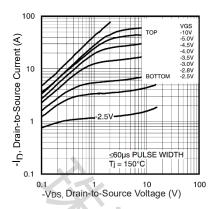


Fig 1. Typical Output Characteristics

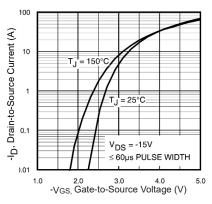


Fig 2. Typical Transfer Characteristics

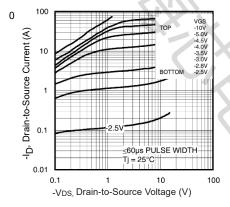


Fig 3. Typical Output Characteristics

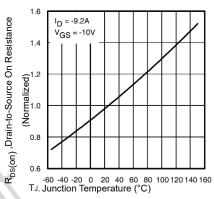


Fig 4. Normalized On-Resistance vs. Temperature

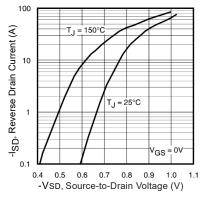


Fig 5. Typical Source-Drain Diode Forward Voltage

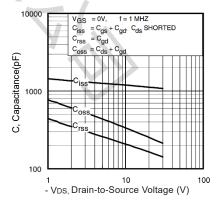


Fig 6. Typical Capacitance Vs.

Drain-to-Source Voltage

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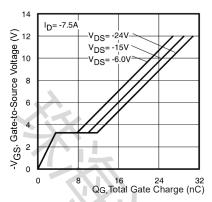


Fig 7. Typical Gate Charge vs.Gate-to-Source Voltage

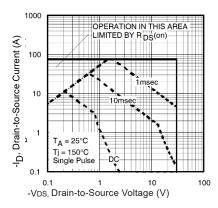


Fig 8.Maximum Safe Operating Area

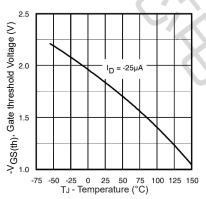


Fig 9. Threshold Voltage vs. Temperature

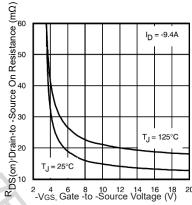


Fig 10. On-Resistance vs. Gate Voltage

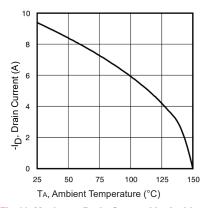


Fig 11. Maximum Drain Current Vs. Ambient Temperature

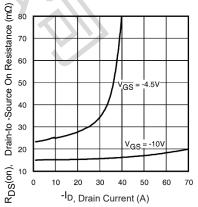


Fig 12. Typical On-Resistance Vs. Drain Current

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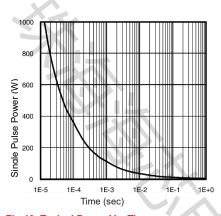


Fig 13. Typical Power Vs. Time

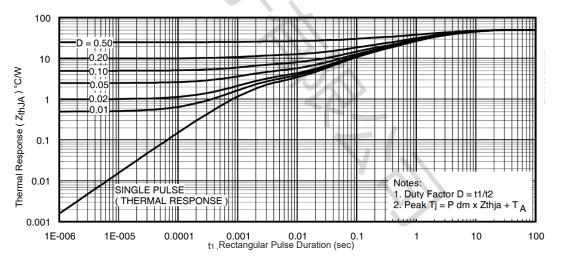
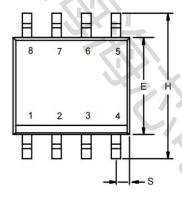


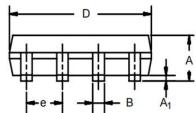
Fig 14. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

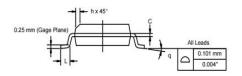
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SOP-8 Package Outline

Dimensions are shown in millimeters (inches)



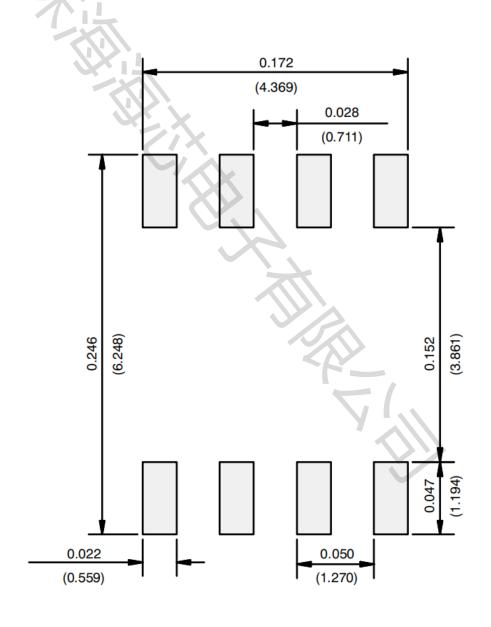




	MILLI	METERS	INCHE		
DIM	Min	Max	Min	Max	
Α	1.35	1.75	0.053	0.069	
A 1	0.10	0.20	0.004	0.008	
В	0.35	0.51	0.014	0.020	
X	0.19	0.25	0.007	0.040	
С		0.25	5	0.010	
D	4.80	5.00	0.189	0.196	
E	3.80	4.00	0.150	0.157	
е	1.27 BSC		0.050 BSC		
Н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.020	
L	0.50	0.93	0.020	0.037	
q	0°	8°	0°	8°	
S	0.44	0.64	0.018	0.026	

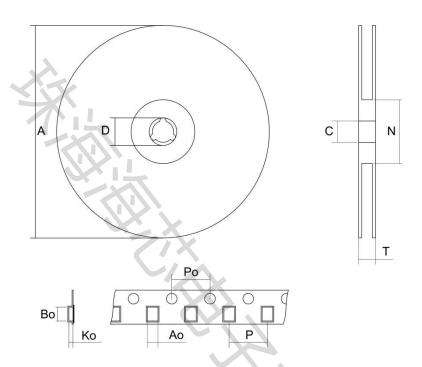
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RECOMMENDED MINIMUM PADS FOR SOP-8

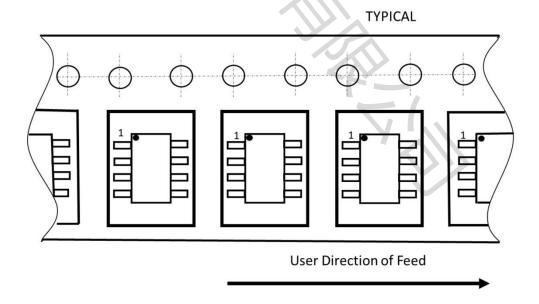


SOP-8 packing information

SO-8 tape and reel



Tape orientation



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